

# P0080SCE

## SMB Plastic-Encapsulate Diodes

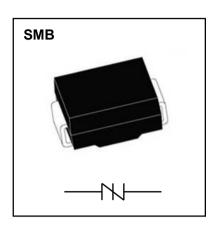
### **Thyristor Surge Suppressors**

#### Features

- Low switching voltage
- Low on-state voltage
- Does not degrade surge capability after multiple surge Events within limit
- Fails short circuit when surged in excess of ratings
- Low Capacitance

### Applications

• Protect circuit



### Electrical Characteristics ( $T_a=25^{\circ}C$ Unless otherwise specified)

Parameter	Definition	
СО	Off-state Capacitance-typical capacitance measured in off state	- +I - t .
di /dt	Rate of Rise of Current —maximum rated value of the acceptable rate of rise in current over time	I
IS	Switching Current-maximum current required to switch to on state	Is/
IDRM	Leakage Current —maximum peak off-state current measured at VDRM	
IH	Holding Current — minimum current required to maintain on state	Idrm
IPP	Peak Pulse Current—maximum rated peak impulse current	$-V \leftarrow \uparrow \uparrow \uparrow \uparrow +V$
ІТ	On-state Current-maximum rated continuous on-state current	
ITSM	Peak One-cycle Surge Current —maximum rated one-cycle AC current	
VS	Switching Voltage — maximum voltage prior to switching to on state	
VDRM	Peak Off-state Voltage —maximum voltage that can be applied while maintaining off state	-I
VF	On-state Forward Voltage —maximum forward voltage measured at rated on-state current	_
VT	On-state Voltage — maximum voltage measured at rated on-state current	_

#### **Electrical Characteristics**

#### Electrical Characteristics (Ta=25°C Unless otherwise specified)

PART NUMBER	Vdrm V Min.	Idrм uA Max.	Vs V Max.	ls mA	V⊤ V Max.	lt A	Iн mA	Co pF Max.
P0080SCE	6	5	25	800	4	2.2	≥50	130

1、Vs is measured at 100KV/S

2. Off-state capacitance is measured in VDc=2V, VRMs=1V, F=1MHz  $\,$ 

3. All measurements are made at an ambient temperature of  $25^\circ\!C$ 

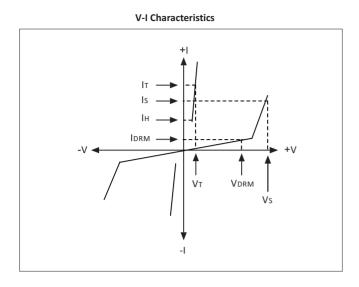
#### **Surge Ratings**

<b>O</b> ution	IPP (A) min				
Series	2 × 10us	8 × 20us	10 ×360us	10 ×1000us	
P0080SCE	400	400	175	100	

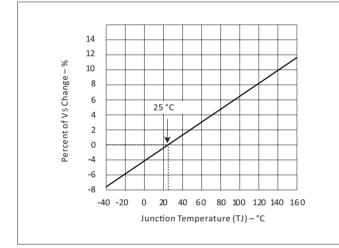
#### Limiting Values (Absolute Maximum Rating)

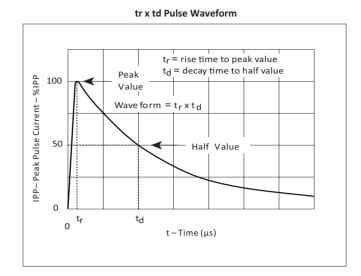
Symbol	Parameter	Value	Unit
ιT	Operating Junction Temperature	-40 to +150	C°
Ts	Storage Temperature Range	-40 to +150	C°
Reja	RejA Junction to Ambient on printed circuit		°C/W

#### **Typical Characteristics**

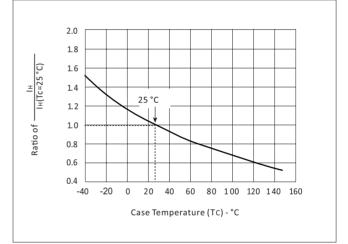


Normalized V Change vs. Junction Temperature

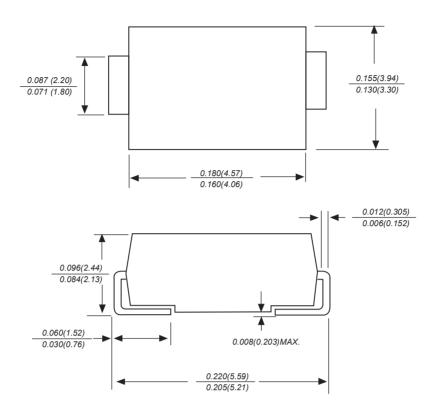




Normalized DC Holding Current vs. Case Temperature

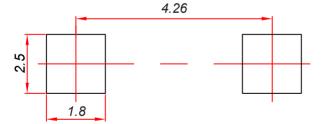


#### SMB Package Outline Dimensions



Dimensions in inches and (millimeters)

#### SMB Suggested Pad Layout



#### Note:

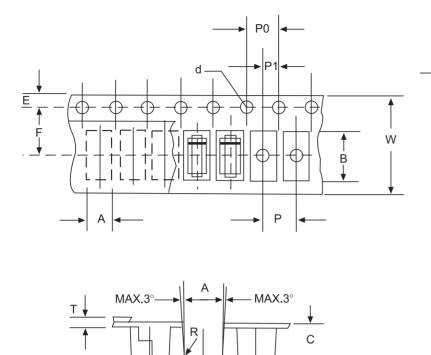
Controlling dimension:in millimeters.
General tolerance:± 0.05mm.
The pad layout is for reference purposes only.

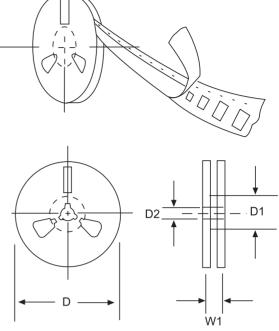
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## **High Diode Semiconductor**

### Reel Taping Specifications For Surface Mount Devices-SMB





#### **FIG:CONFIGURATION OF AXIAL TAPING**

ITEM	SYMBOL	SMB mm(inch)
Carrier width	A	4.09±0.1(0.161±0.004)
Carrier length	В	5.82±0.1(0.229±0.004)
Carrier depth	С	3.33±0.1(0.131±0.004)
Sprocket hole	d	1.55±0.05(0.061±0.0002
Reel outside diameter	D	330/178±2.0(13/7.0±0.79)
Reel inner diameter	D1	8.0±0.2(0.315±0.008)
Feed hole diameter	D2	13±0.5(0.512±0.020)
Strocket hole position	E	1.75±0.1(0.069±0.004)
Punch hole position	F	5.65±0.05(0.222±0.002)
Punch hole pitch	Р	8.0±0.1(0.315±0.004)
Sprocket hole pitch	P0	4.0±0.1(0.157±0.004)
Embossment center	P1	2.0±0.1(0.079±0.004)
Totall tape thickness	Т	0.32±0.1(0.013±0.004)
Tape width	W	12.0±0.2(0.472±0.008)
Reel width	W1	16.8±2.0(0.661±0.079)

NOTE:Devices are packde in accordance with EIA standard RS-481-A and specification given above.

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